

Jan Van Houdt

List of Publications by Year in descending order

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Version: 2024-02-01

30
papers

413
citations

759233

12
h-index

794594

19
g-index

31
all docs

31
docs citations

31
times ranked

422
citing authors

#	ARTICLE	IF	CITATIONS
1	Reliability Study of Ferroelectric Al:HfO ₂ Thin Films for DRAM and NAND Applications. IEEE Transactions on Electron Devices, 2017, 64, 4091-4098.	3.0	56
2	On the Characterization and Separation of Trapping and Ferroelectric Behavior in HfZrO FET. IEEE Journal of the Electron Devices Society, 2019, 7, 855-862.	2.1	39
3	Cross-cell interference variability aware model of fully planar NAND Flash memory including line edge roughness. Microelectronics Reliability, 2011, 51, 919-924.	1.7	31
4	Physical Model for the Steep Subthreshold Slope in Ferroelectric FETs. IEEE Electron Device Letters, 2018, 39, 877-880.	3.9	27
5	Defect profiling in FEFET Si:HfO ₂ layers. Applied Physics Letters, 2020, 117, .	3.3	23
6	Compact Modeling of Multidomain Ferroelectric FETs: Charge Trapping, Channel Percolation, and Nucleation-Growth Domain Dynamics. IEEE Transactions on Electron Devices, 2021, 68, 2107-2115.	3.0	21
7	Charge-based nonvolatile memory: Near the end of the roadmap?. Current Applied Physics, 2011, 11, e21-e24.	2.4	18
8	Investigation of Imprint in FE-HfO ₂ , and Its Recovery. IEEE Transactions on Electron Devices, 2020, 67, 4911-4917.	3.0	18
9	First principles investigation of charge transition levels in monoclinic, orthorhombic, tetragonal, and cubic crystallographic phases of HfO ₂ . Journal of Applied Physics, 2021, 129, .	2.5	17
10	Physical understanding and modeling of SANOS retention in programmed state. Solid-State Electronics, 2008, 52, 577-583.	1.4	16
11	High-Endurance Ferroelectric (La, Y) and (La, Gd) Co-Doped Hafnium Zirconate Grown by Atomic Layer Deposition. ACS Applied Electronic Materials, 2022, 4, 1823-1831.	4.3	15
12	Positive non-linear capacitance: the origin of the steep subthreshold-slope in ferroelectric FETs. Scientific Reports, 2019, 9, 14957.	3.3	14
13	Electrical Investigation of Wake-Up in High Endurance Fatigue-Free La and Y Doped HZO Metal "Ferroelectric" Metal Capacitors. IEEE Transactions on Electron Devices, 2022, 69, 4744-4749.	3.0	14
14	New Insights into the Imprint Effect in FE-HfO ₂ and its Recovery. , 2019, , .		12
15	Physical Insights on Steep Slope FEFETs including Nucleation-Propagation and Charge Trapping. , 2019, , .		12
16	Program/Erase Scheme for Suppressing Interface Trap Generation in HfO ₂ -Based Ferroelectric Field Effect Transistor. IEEE Electron Device Letters, 2021, 42, 1280-1283.	3.9	12
17	Ferroelectric La-Doped ZrO ₂ /HfO ₂ /ZrO ₂ Bilayer Stacks with Enhanced Endurance. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100033.	2.4	11
18	Strain and ferroelectricity in wurtzite ScxAl1-xN materials. Applied Physics Letters, 2021, 119, .	3.3	11

#	ARTICLE	IF	CITATIONS
19	Impact of Charge Trapping and Depolarization on Data Retention Using Simultaneous P and V in HfO_2 -Based Ferroelectric FET. IEEE Transactions on Electron Devices, 2021, 68, 4391-4396.	3.0	10
20	Impact of Ferroelectric Wakeup on Reliability of Laminate based Si-doped Hafnium Oxide (HSO) FeFET Memory Cells. , 2020, , .		7
21	Probing the Evolution of Electrically Active Defects in Doped Ferroelectric HfO_2 during Wake-Up and Fatigue. , 2020, , .		6
22	Understanding the memory window in 1T-FeFET memories: a depolarization field perspective. , 2021, , .		5
23	Low-frequency noise assessment of ferro-electric field-effect transistors with Si-doped HfO_2 gate dielectric. AIP Advances, 2021, 11, .	1.3	4
24	Identifying alternative ferroelectric materials beyond $Hf(Zr)O_2$. Applied Physics Letters, 2020, 117, 262903.	3.3	3
25	Trap-polarization interaction during low-field trap characterization on hafnia-based ferroelectric gatestacks. , 2022, , .		3
26	A comprehensive variability study of doped HfO_2 FeFET for memory applications. , 2022, , .		3
27	Trades-off between lithography line edge roughness and error-correcting codes requirements for NAND Flash memories. Microelectronics Reliability, 2012, 52, 525-529.	1.7	2
28	Impacts of Pulsing Schemes on the Endurance of Ferroelectric Metal-Insulator-Semiconductor Capacitors. IEEE Journal of the Electron Devices Society, 2022, 10, 109-114.	2.1	2
29	Endurance of ferroelectric La-doped HfO_2 for SFS gate-stack memory devices. , 2020, , .		1
30	Impact of interface layer on charge trapping in $Si:HfO_2$ based FeFET. , 2020, , .		0